

REMARKS

Claims 111, 112, 115, 116, 119, 120, 124-128, 130, 134-136, 138-141, 144, 145, 148, 150-154, 156-158, 160 and 162 have been amended. No new matter has been added. Claims 123, 133, 137, 149 and 163 have been canceled and their subject matter incorporated into claims 111, 126, 136, 148 and 157, respectively. Claims 1-110, 113, 114, 142, 143 and 159 were previously canceled. Claims 111, 112, 115-122, 124-132, 134-136, 138-141, 144-148, 150-158 and 160-162 are currently pending in this application. Applicant reserves the right to pursue the original and other claims in this and other applications.

Claims 111, 112, 115-141, 144-158 and 160-163 stand rejected under 35 U.S.C. § 103(a) as being unpatentable in view of Kwok et al. (U.S. Patent No. 6,373,088) ("Kwok") in view of Lou (U.S. Patent No. 6,235,579) ("Lou") and Chang et al. (U.S. Patent Application Publication 2002/0137284) ("Chang"). The rejection is respectfully traversed and reconsideration is respectfully requested.

Claims 111 and 126 each recite a metal-polysilicon contact including a "plurality of layers capable of absorbing oxygen." The "plurality of layers capable of absorbing oxygen" are "formed adjacent to and in contact with said at least one conductive layer," "are separated by said at least one conductive layer," and "are formed within said opening of said insulating layer."

Claims 136, 148 and 157 each recite a metal-polysilicon contact including a "plurality of oxygen sink layers." The "plurality of oxygen sink layers" are "formed adjacent to and in contact with said at least one conductive layer," "are separated by said at least one conductive layer," and "are formed within said opening of said insulating layer."

Kwok relates to an integrated circuit structure formed to have reduced edge stress. (Kwok, col. 1, lines 9-10). Lou relates to a method of manufacturing a stacked capacitor with decreased fabrication costs and chemical interaction between layers. (Lou, col. 2, line 59 - col. 3, line 45). Chang relates to a method of manufacturing high-density integration semiconductor memory devices where the control gate electrode is resistant to oxidation during high temperature processing in an oxidizing ambient. (Chang, ¶[0010]-[0011]).

None of Kwok, Lou or Chang disclose, teach or suggest a metal-polysilicon structure including a “plurality of layers capable of absorbing oxygen” or a “plurality of oxygen sink layers,” let alone a plurality of such layers that are “formed adjacent to and in contact with said at least one conductive layer,” “are separated by said at least one conductive layer,” and “are formed within said opening of said insulating layer” as recited in each of claims 111, 126, 135, 148 and 157. Each of these references shows only one structure (e.g., the dielectric layer 240 of Kwok, layer 210a of Lou, and layer 11 of Chang) allegedly corresponding to the oxygen absorbing/oxygen sink layers of the claimed invention. Accordingly, none of the cited references, alone or in combination disclose, teach or suggest a plurality of such layers that are “formed adjacent to and in contact with said at least one conductive layer,” “are separated by said at least one conductive layer,” and “are formed within said opening of said insulating layer.”

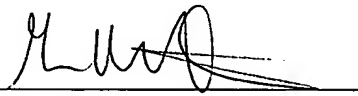
Accordingly, claims 111, 126, 136, 148 and 157 are patentable in view of the cited combination. Claims 112, 115-122 and 125 depend from claim 111 and are allowable along with claim 111. Claims 127-132, 134 and 135 depend from claim 126 and are allowable along with claim 126. Claims 138-141 and 144-147 depend from claim 136 and are allowable along with claim 136. Claims 150-156 depend from claim 148 and are allowable along with claim 148. Claims 158 and 160-162 depend from claim 157 and are allowable along with claim 157. Claims 123, 133, 137, 149 and 153 have been

canceled. Applicant respectfully requests that the rejection of claims 111, 112, 115-122, 124-132, 134-136, 138-141, 144-148, 150-158 and 160-162 be withdrawn and the claims be allowed.

In view of the above amendment, Applicant believes the pending application is in condition for allowance.

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